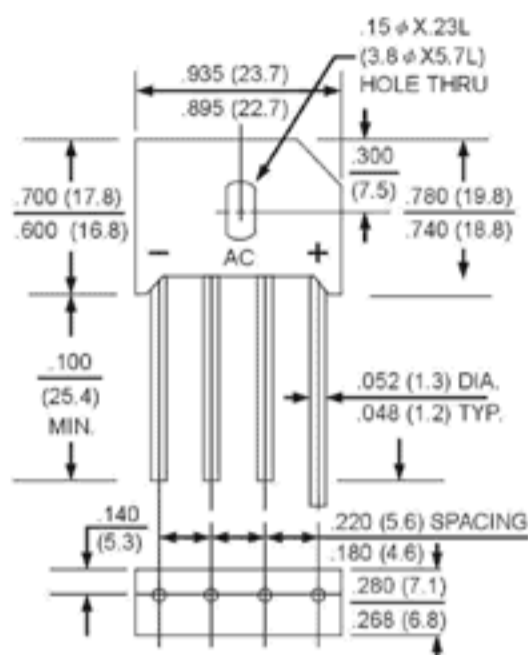


SILICON BRIDGE RECTIFIERS

REVERSE VOLTAGE - 50 to 1000 Volts
FORWARD CURRENT - 10/15/25/35 Amperes

FEATURES

- Surge overload rating - 240~400 amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Plastic material has Underwriters Laboratory Flammability classification 94V-0
- Mounting Position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	KBU	KBU	KBU	KBU	KBU	KBU	KBU	UNIT
		10A	10B	10D	10G	10J	10K	10M	
		15A	15B	15D	15G	15J	15K	15M	
		25A	25B	25D	25G	25J	25K	25M	
		35A	35B	35D	35G	35J	35K	35M	
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @T _C =100°C (without heatsink)	I _(AV)	10/15/25/35 3.2							A
Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC Method)	I _{FSM}	10A: 240 15A: 240 25A: 350 35A: 400							A
Maximum Forward Voltage at 5.0/ 7.5/12.5/17.5A DC	V _F	1.0							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	@T _J = 25 °C: 10 @T _J =125°C: 500							uA
I ² t Rating for fusing (t<8.3ms)	I ² t	240							A ² S
Typical Junction Capacitance per element (Note 1)	C _J	60							pF
Typical Thermal Resistance (Note 2)	R _{θJC}	0.8							°C/W
Operating Temperature Range	T _J	-40 to +125							°C
Storage Temperature Range	T _{STG}	-40 to +125							°C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Device mounted on 300mm x 300mm x 1.6mm Cu Plate Heatsink.